

INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)	Docket Number (Optional) TWI-12030	Application Number NEW
	Applicant(s) Jon Opsal et al	
	Filing Date HEREWITH	Group Art Unit Unknown

U.S. PATENT DOCUMENTS

*EXMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>h</i>	*A	4,200,396	04/29/1980	Kleinknecht et al.	356	636	12/19/1977
<i>h</i>	*B	4,408,884	10/11/1983	Kleinknecht et al.	356	496	06/29/1981
<i>h</i>	*C	4,999,014	03/12/1991	Gold et al.	356	382	05/04/1989
<i>h</i>	*D	5,042,951	08/27/1991	Gold et al.	356	369	09/19/1989
<i>h</i>	*E	5,159,412	10/27/1992	Willenborg et al.	356	445	03/15/1991
<i>h</i>	*F	5,412,473	05/02/1995	Rosencwaig et al.	356	351	07/16/1993
<i>h</i>	*G	5,703,692	12/30/1997	McNeil et al.	356	445	08/03/1995
<i>h</i>	*H	5,739,909	04/14/1998	Blayo et al.	356	369	10/10/1995
<i>h</i>	*I	5,830,611	11/03/1998	Bishop et al.	430	30	03/05/1992
<i>h</i>	*J	5,867,276	02/02/1999	McNeil et al.	356	445	03/07/1997
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<i>h</i>	*L	5,917,594	06/29/1999	Norton	356	327	04/08/1998
<i>h</i>	*M	6,137,570	10/24/2000	Chuang et al.	356	237.5	06/30/1998
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							YES	NO
<i>h</i>	*O	WO 99/02970	01/21/1999	PCT	G01N	21/21		
<i>h</i>	*P	WO 99/45340	09/10/1999	PCT	G01B	11/02		

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<i>h</i>	*Q	J. Bao et al., "Specular Spectral Profilometry on Metal Layers," (Seminar Proceedings: Metrology, Inspection, and Process Control for Microlithography XIV) <i>Proceedings of SPIE</i> , Vol. 3998, 2000, pp. 882-892.
<i>h</i>	*R	C.J. Raymond et al., "Multi-parameter process metrology using scatterometry," <i>SPIE</i> , Vol. 2638, 1995, pp. 84-93.
<i>h</i>	*S	M.R. Murnane et al., "Scatterometry for 0.24 μ m - 0.70 μ m developed photoresist metrology, <i>SPIE</i> , Vol. 2439, 1995, pp. 427-436.
<i>h</i>	*T	P.A. Heimann et al., "Optical Etch-Rate Monitoring: Computer Simulation of Reflectance," <i>J. Electrochem. Soc.</i> , Vol. 131, No. 4, April 1984, pp. 881-885.
<i>h</i>	*U	P.A. Heimann, "Optical Etch-Rate Monitoring Using Active Device Areas: Lateral Interference Effects," <i>J. Electrochem. Soc.</i> , Vol. 132, No. 8, August 1985, pp. 2003-2006.

Examiner <i>Richard Rosenh</i>	Date Considered <i>15 March 2004</i>
Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include Copy of this form with next communication to applicant.	